

**PN: K0-0850M-0000-00017**  
**Die/Assy; 850; M; P10X40; 4W; 1.26mm x 1.26mm**

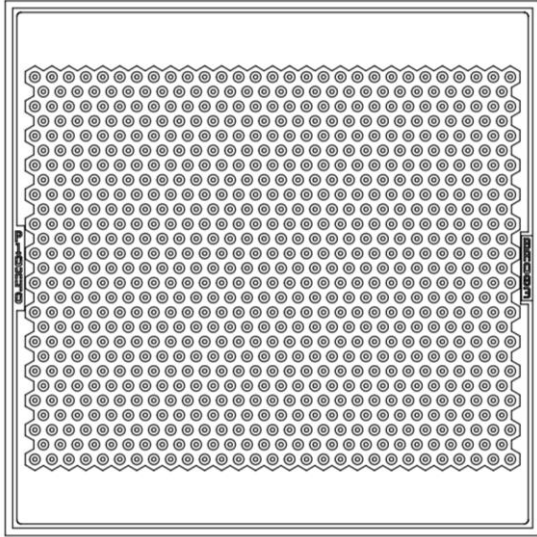


Figure 1 Bare die

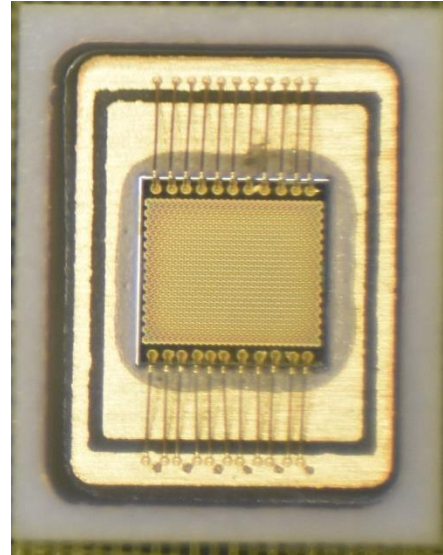


Figure 2 Ceramic package

**Near Infra-Red Vertical Cavity Surface Emitting Laser (VCSEL)**

Model: Multi Mode Array VCSEL  
Center wavelength: 850nm  
Optical power without diffuser: 4 Watts

**Applications**

- Motion Control
- Time of Flight
- Automotive Sensing
- 3D Scanning
- Motion Control
- Time of Flight
- Gesture Recognition
- IR illumination for Security



COMPLIES WITH IEC 60825-1, 2<sup>nd</sup> Edition 2007.  
COMPLIES WITH 21 CFR 1040.10 AND 1040-10.11 EXCEPT FOR DEVIATIONS PURSUANT TO LASER NOTICE NO.50 DATED 27 MAY 2001.

## Absolute Maximum Ratings

Parameter	Rating	Notes
Storage temperature	-40 to 100 °C	
Operating temperature (VCSEL)	-20 to 85 °C	
Maximum package SMT solder reflow temperature	260°C, 10 seconds	
Maximum pulsed current	8 A	≤ 200 μs pulse width, ≤ 10% duty cycle, Temp ≤ 40 °C, Note 1
Laser reverse voltage	5 V	Note 1
ESD damage threshold	±2kV	MIL_STD-883D, Method 3015.7 human body model, Note 1

Note 1 Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only. Functional operation of the device at these or any other conditions beyond those indicated for extended periods of time may affect device reliability.

## Electro-Optical Characteristics

VCSEL Operating Temp (T<sub>v</sub>) = 40 °C, Test condition: 100μs pulse width & 10% duty cycle unless otherwise noted. Die performance parameters require the VCSEL die to have adequate heat sinking and proper thermal management.

Parameter	Symbol	Units	Without Diffuser			With Diffuser			Notes
			Min	Typ.	Max	Min	Typ.	Max	
Threshold current	I <sub>th</sub>	A	--	0.80	--	--	0.80	--	
Differential resistance	R <sub>s</sub>	Ω	--	0.2	--	--	0.2	--	
Operating voltage	V <sub>f</sub>	V	--	2.1	2.5	--	2.1	2.5	at I = 5 A
Optical operating power	L <sub>op</sub>	W	--	4.2	--	--	3.65	--	at I = 5 A
Slope efficiency	SE	W/A	--	0.85	--	--	0.68	--	at I = 5 A
Power conversion efficiency	PCE	%	--	40	--	--	35	--	at I = 5 A
Breakdown voltage	V <sub>rb</sub>	V	--	-10	-8	--	-10	-8	I <sub>rb</sub> = -1 μA
Beam divergence	FWHM	deg	17	23	29	N/A	N/A	N/A	For parts with diffusers, see diffuser angle table
Beam divergence	1/e <sup>2</sup>	deg	22	28	34	N/A	N/A	N/A	
Operating peak wavelength	WL <sub>peak</sub>	nm	840	850	860	840	850	860	
Wavelength-Temp tuning		nm/°C	--	0.059	--	--	0.059	--	
Rise time		ps	--	--	800	--	--	--	20%-80% Note 2
Fall time		ps	--	--	1000	--	--	--	20%-80% Note 2

Electro-Optical Characteristic with a diffuser would require further evaluation. Values are based on limited sample size and estimated values.

**Note 2:** Rise and Fall time will vary depending on driver board and electrical layout.

## Diffuser characteristics

Parameter	Symbol	Units	Diffuser Angle						Notes
			72X58			60X45			
			Min	Typ	Max	Min	Typ	Max	
FOV aligned to short length of diffuser	FOVS	deg	--	58	--	--	45	--	FWHM defined by manufacturer
FOV aligned to longer length of diffuser	FOVL	deg	--	72	--	--	60	--	FWHM defined by manufacturer
Diffuser Uniformity	U	%	--	80	-	--	80	-	Note 2
Diffuser Efficiency	%Eff	%	80	90	-	80	90	-	Total transmission efficiency without AR Coating

**Note 2:** The uniformity is measured by projecting the VCSEL with diffuser onto a flat surface and capturing a high-resolution image of the beam profile. Over all the pixels in the eFOV on the image, the mean and standard deviation is calculated. The uniformity is calculated by dividing the difference of the mean and standard deviation by the mean. This is represented as a percentage.

**Note 3:** For all other diffuser options contact Vixar at [sales@vixarinc.com](mailto:sales@vixarinc.com)

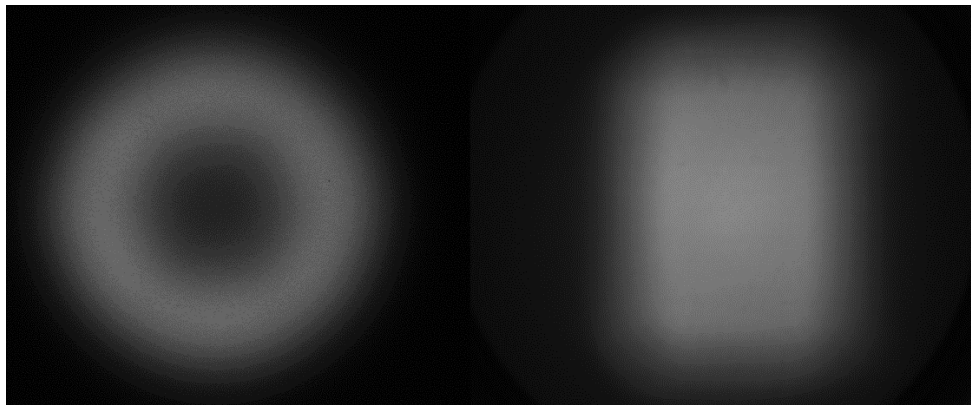


Figure 3 Left, Beam profile without diffuser. Right, Beam profile with rectangular diffuser.

## Typical L-I-V Performance

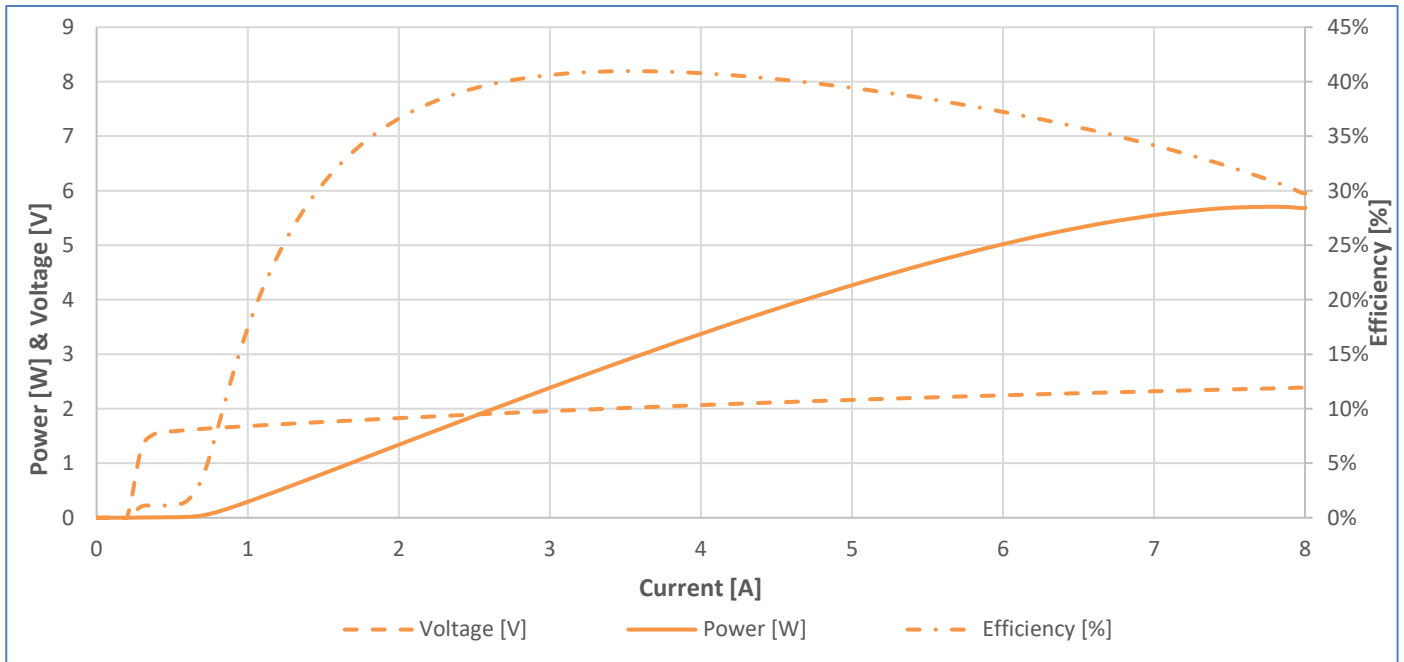


Figure 4 Typical 850nm 4W LIV at 25°C, 100µs pulse width, 1% Duty Cycle in a Ceramic package

## Typical Beam Profile

Note: Beam divergence data for many VCSEL arrays are shown.

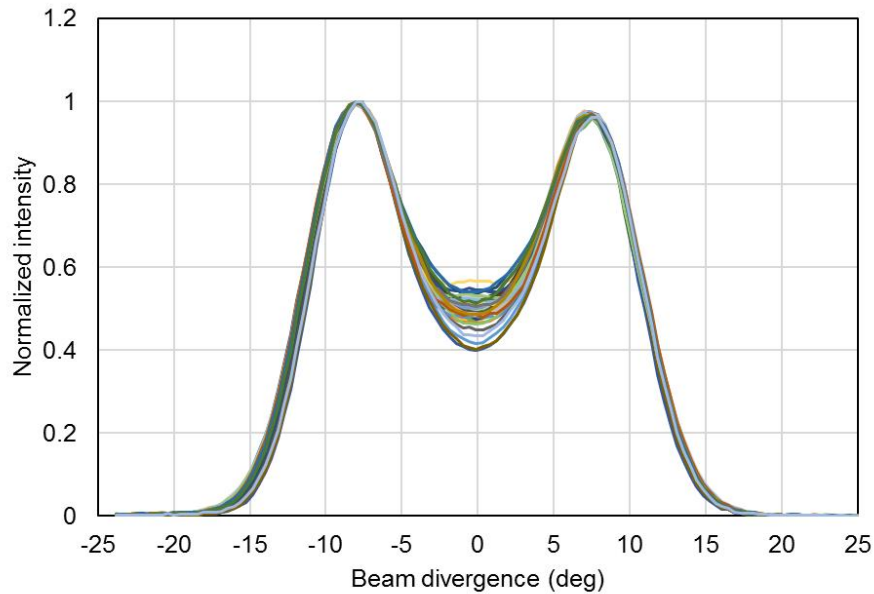


Figure 5 Typical beam divergence of bare die (without diffuser) at 40°C with a 5A current injection

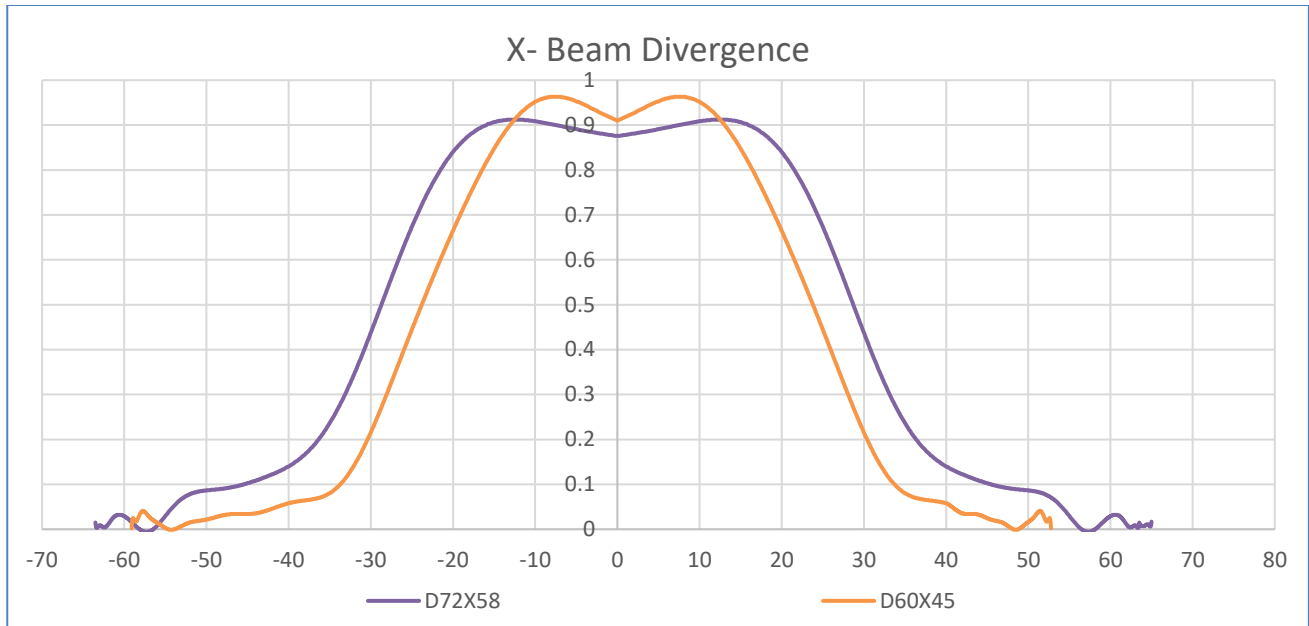


Figure 6 X-direction beam divergence with their respective diffuser at 25°C, 5A. Operational Mode: 100µS, 10% Duty Cycle.

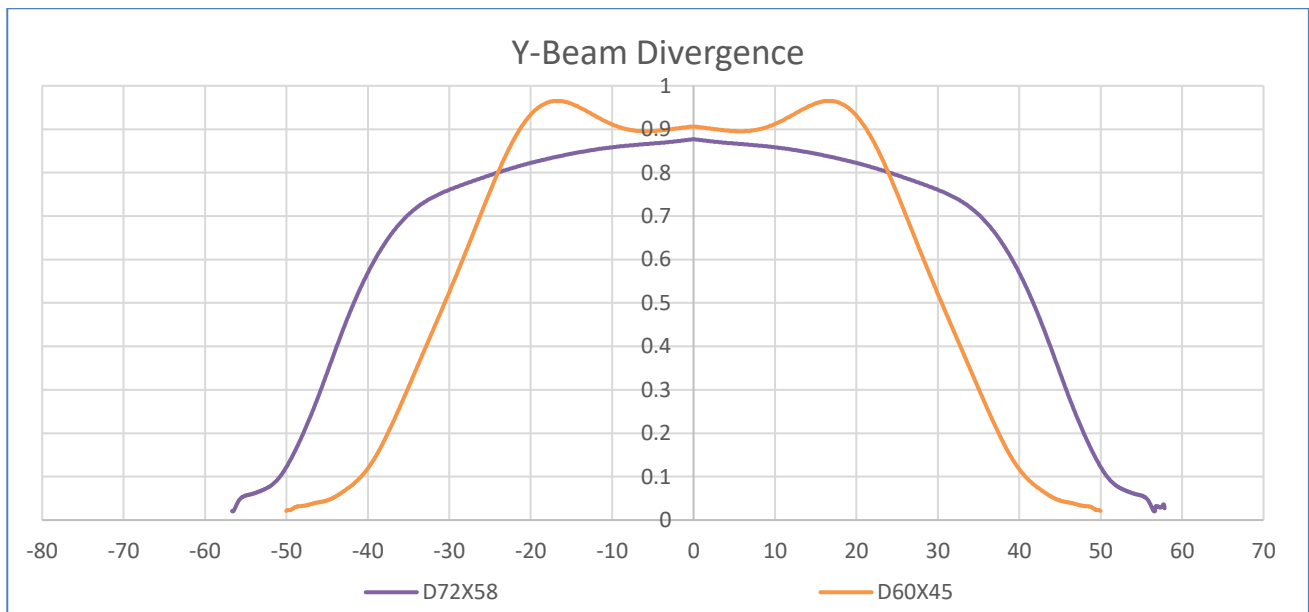
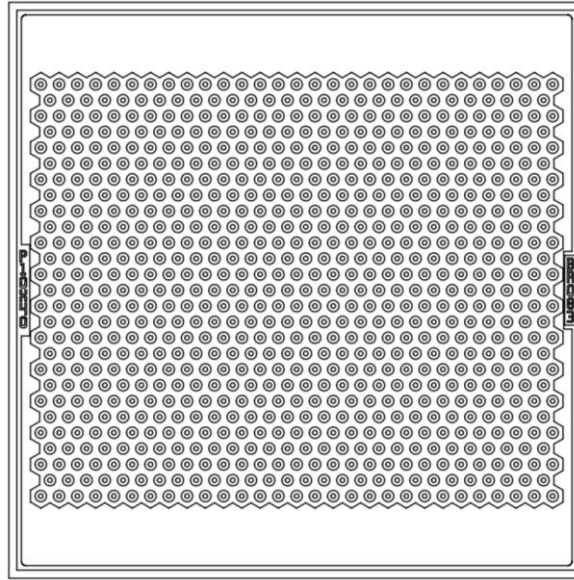


Figure 7 Y-direction beam divergence with their respective diffuser at 25°C, 5A. Operational Mode: 100µS, 10% Duty Cycle.

## VCSEL Mechanical Specification



Parameter	Specification
Die size (x / y) final	1.260 mm X 1.260 mm
Number of Apertures	770
Die thickness	100µm

## Ordering Information

Description	Package	Part Number
Die;850;MM; 3B; P10x40;4W;1.26mm X 1.26mm	Bare Die	K0-0850M-0000-00017
Assy;850;MM; 3B; P10x40;4W;1.26mm X 1.26mm; C2835-2L; D60x45	Ceramic	K0-0850M-0000-00049
Assy;850;MM; 3B; P10x40;4W;1.26mm X 1.26mm; C2835-2L; D72x58	Ceramic	K0-0850M-0000-00072
Assy;850;MM;3B;P10x40;4W;1.26mm X 1.26mm; C2835-2L	Ceramic	K0-0850M-0000-00053

**Vixar**  
**OSRAM**

**Opto Semiconductors**

2950 Xenium Lane, Suite 104

Plymouth, MN 55441

763-746-8045

email: info@vixarinc.com

website: www.vixarinc.com

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